

High Voltage Power MOSFET

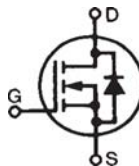
IXTF03N400

$$V_{DSS} = 4000V$$

$$I_{D25} = 300mA$$

$$R_{DS(on)} \leq 300\Omega$$

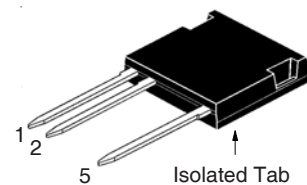
(Electrically Isolated Tab)



N-Channel Enhancement Mode

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	4000	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	4000	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	300	mA
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	800	mA
P_D	$T_C = 25^\circ C$	70	W
T_J		- 55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		- 55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
F_C	Mounting Force	20..120 / 4.5..27	N/lb.
V_{ISOL}	50/60Hz, 1 Minute	4000	V~
Weight		5	g

ISOPLUS i4-Pak™



1 = Gate
2 = Source
5 = Drain

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 4000V Electrical Isolation
- Molding Epoxies meet UL 94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

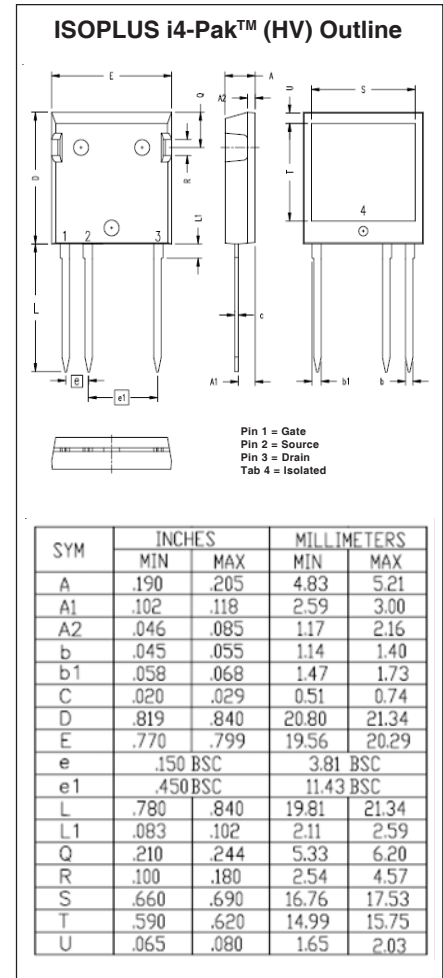
- High Voltage Power Supplies
- Capacitor Discharge
- Pulse Circuits

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	4000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ Note 2, $T_J = 125^\circ C$			10 μA 750 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			300 Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 50\text{V}$, $I_D = 100\text{mA}$, Note 1	110	180	mS
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		435	pF
C_{oss}			19	pF
C_{rss}			6	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 250\text{V}$, $I_D = 150\text{mA}$ $R_G = 50\Omega$ (External)		17	ns
t_r			16	ns
$t_{d(off)}$			86	ns
t_f			58	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 1\text{kV}$, $I_D = 0.5 \cdot I_{D25}$		16.3	nC
Q_{gs}			1.9	nC
Q_{gd}			8.8	nC
R_{thJC}			1.78	$^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$			300 mA
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			1.2 A
V_{SD}	$I_F = 300\text{mA}$, $V_{GS} = 0\text{V}$, Note 1			3.0 V
t_{rr}	$I_F = 1\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 200\text{V}$		2.8	μs



- Notes: 1. Pulse test, $t < 300\mu\text{s}$, duty cycle, $d < 2\%$.
2. Device must be heatsunk for high-temperature leakage current measurements to avoid thermal runaway.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

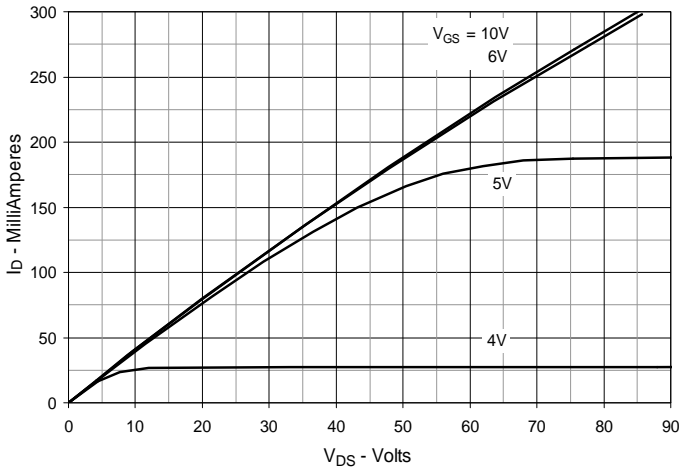


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

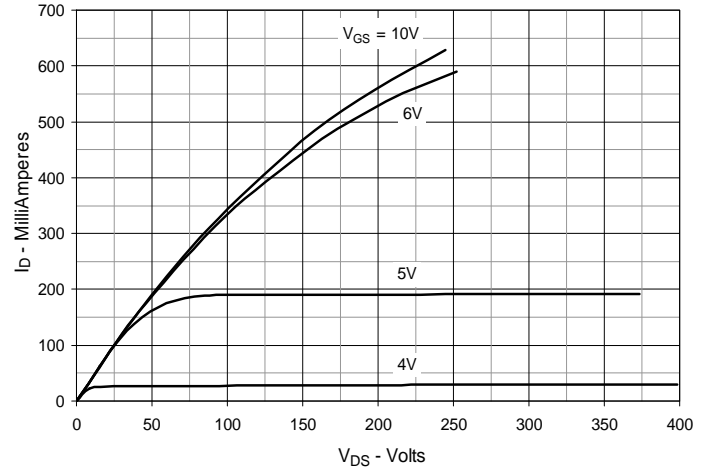


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

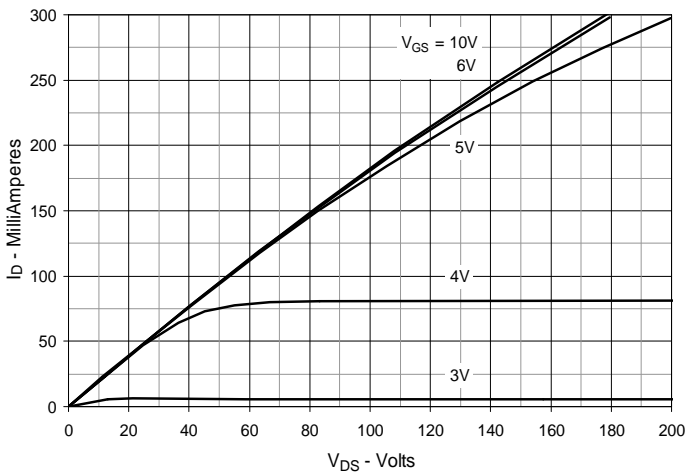


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 150\text{mA}$ Value vs. Junction Temperature

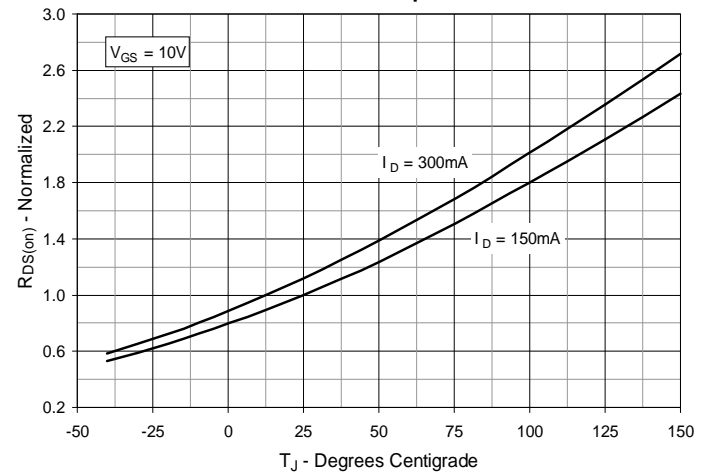


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 150\text{mA}$ Value vs. Drain Current

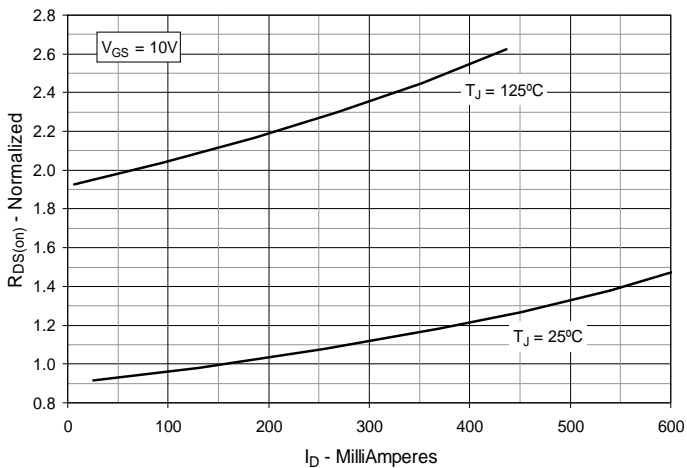


Fig. 6. Maximum Drain Current vs. Case Temperature

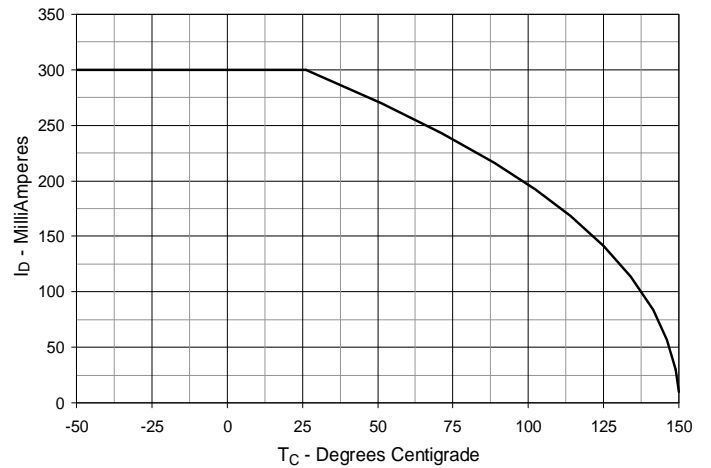


Fig. 7. Input Admittance

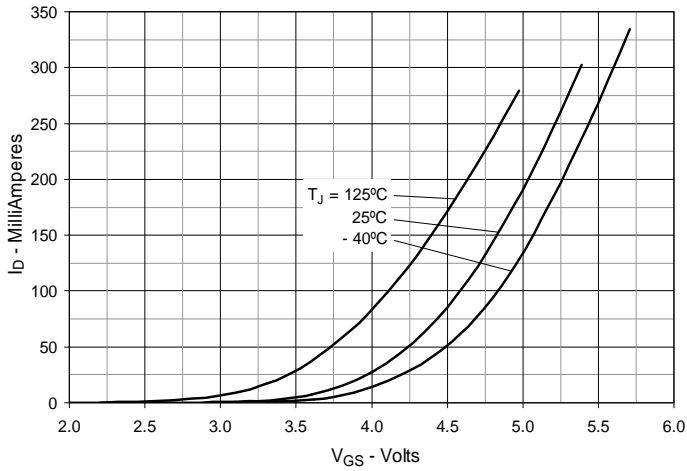


Fig. 8. Transconductance

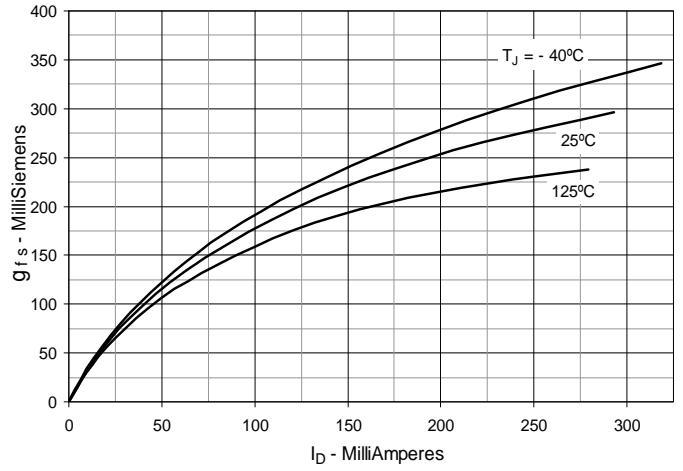


Fig. 9. Forward Voltage Drop of Intrinsic Diode

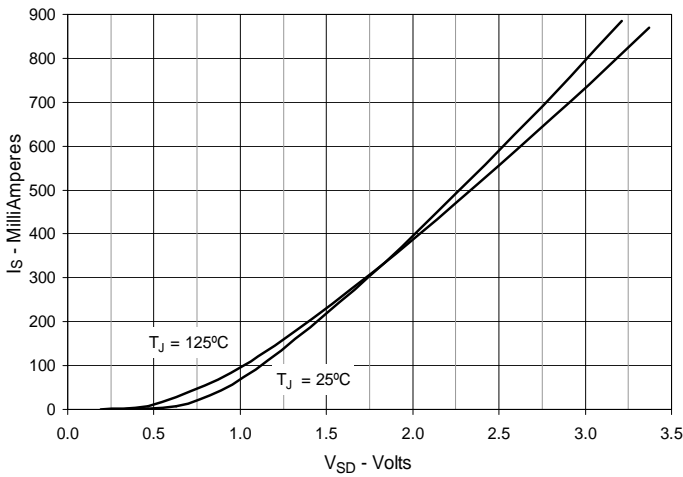


Fig. 10. Gate Charge

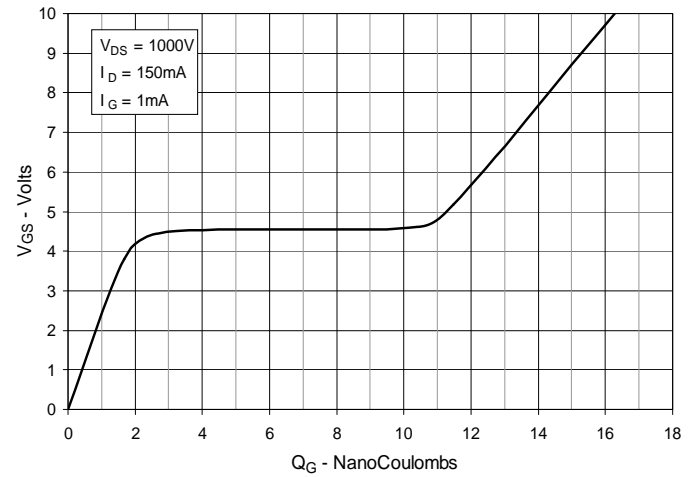


Fig. 11. Capacitance

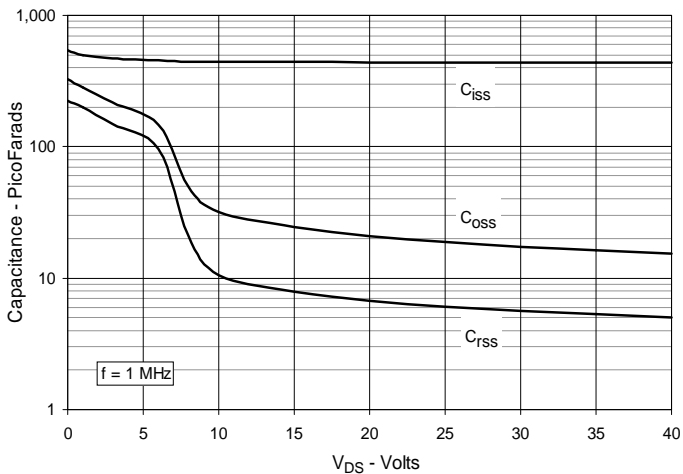


Fig. 12. Maximum Transient Thermal Impedance

